



# 2SB772

## PNP medium power transistor

### Features

- High current
- Low saturation voltage
- Complement to 2SD882

### Applications

- Voltage regulation
- Relay driver
- Generic switch
- Audio power amplifier
- DC-DC converter

### Description

The device is a PNP transistor manufactured by using planar Technology resulting in rugged high performance devices. The complementary NPN type is 2SD882.

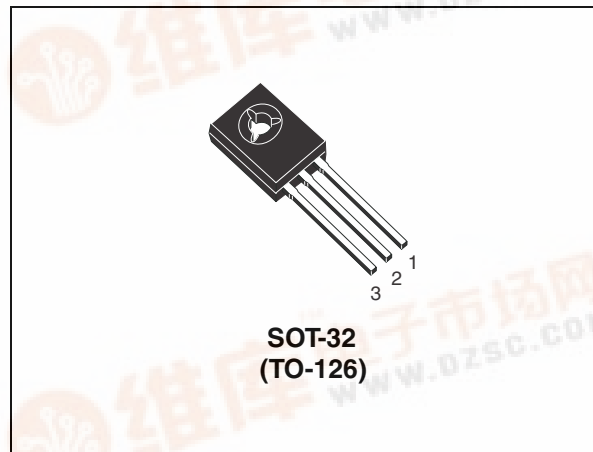


Figure 1. Internal schematic diagram

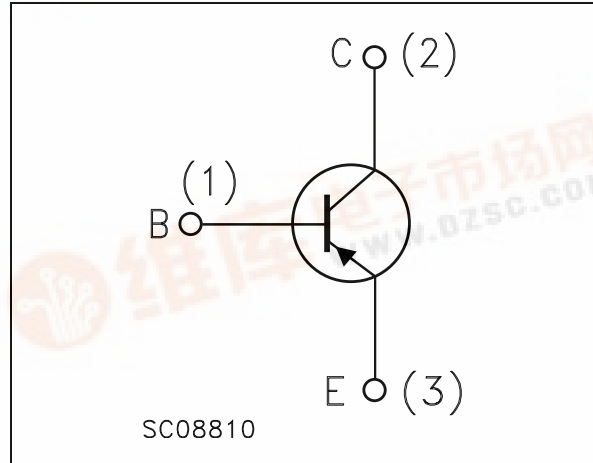


Table 1. Device summary

Order code	Marking	Package	Packing
2SB772	B772	SOT-32	Tube



# 1 Absolute maximum ratings

**Table 2. Absolute maximum rating**

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-base voltage ( $I_E = 0$ )	-60	V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	-30	V
$V_{EBO}$	Collector-base voltage ( $I_C = 0$ )	-5	V
$I_C$	Collector current	-3	A
$I_{CM}$	Collector peak current ( $t_p < 5\text{ms}$ )	-6	A
$I_B$	Base current	-1	A
$I_{BM}$	Base peak current ( $t_p < 5\text{ms}$ )	-2	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	12.5	W
$T_{STG}$	Storage temperature	-65 to 150	$^\circ\text{C}$
$T_J$	Max. operating junction temperature	150	$^\circ\text{C}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJ-case}$	Thermal resistance junction-case max	10	$^\circ\text{C/W}$

## 2 Electrical characteristics

( $T_{CASE} = 25^{\circ}C$ ; unless otherwise specified)

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{CES}$	Collector cut-off current ( $V_{BE} = 0$ )	$V_{CE} = -60$ V			-10	$\mu A$
$I_{CEO}$	Collector cut-off current ( $I_B = 0$ )	$V_{CE} = -30$ V			-100	$\mu A$
$I_{EBO}$	Emitter cut-off current ( $I_C = 0$ )	$V_{EB} = -5$ V			-10	$\mu A$
$V_{(BR)CEO(1)}$	Collector-emitter breakdown voltage ( $I_B = 0$ )	$I_C = -10$ mA	-30			V
$V_{(BR)CBO}$	Collector-base breakdown voltage ( $I_E = 0$ )	$I_C = -100$ $\mu A$	-60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage ( $I_C = 0$ )	$I_E = -100$ $\mu A$	-5			V
$V_{CE(sat)(1)}$	Collector-emitter saturation voltage	$I_C = -1$ A $I_B = -50$ mA $I_C = -2$ A $I_B = -100$ mA $I_C = -3$ A $I_B = -150$ mA			-0.4 -0.7 -1.1	V V V
$V_{BE(sat)(1)}$	Base-emitter saturation voltage	$I_C = -2$ A $I_B = -100$ mA			-1.2	V
$h_{FE}$	DC current gain	$I_C = -100$ mA $V_{CE} = -2$ V $I_C = -1$ A $V_{CE} = -2$ V $I_C = -3$ A $V_{CE} = -2$ V	100 80 30		300	
$f_T$	Transition frequency	$I_C = -0.1$ $V_{CE} = -10$ V		100		MHz

1. Pulsed duration = 300 ms, duty cycle  $\leq 1.5\%$ .

## 2.1 Typical characteristics (curves)

Figure 2. Reverse biased safe operating area Figure 3. DC current gain

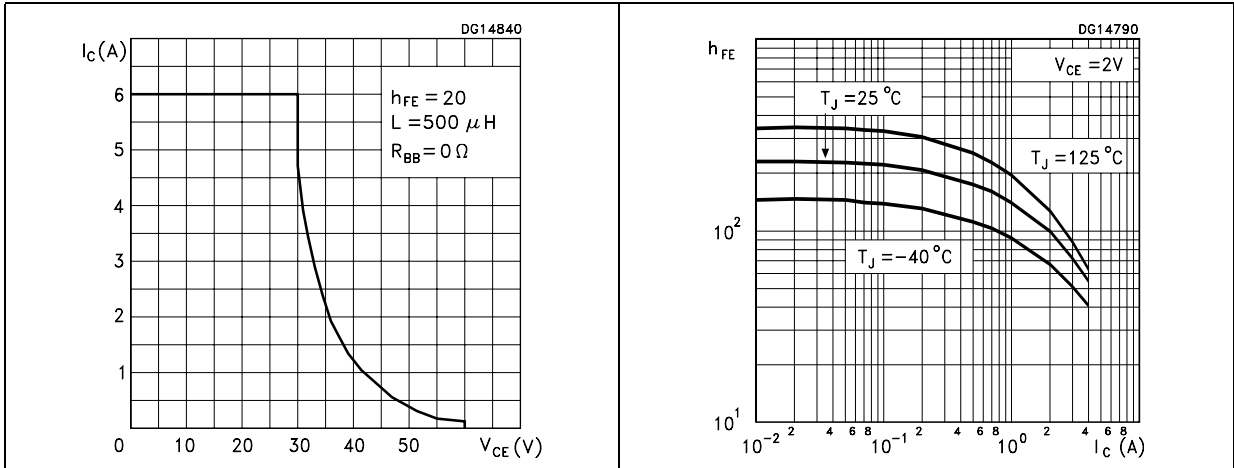
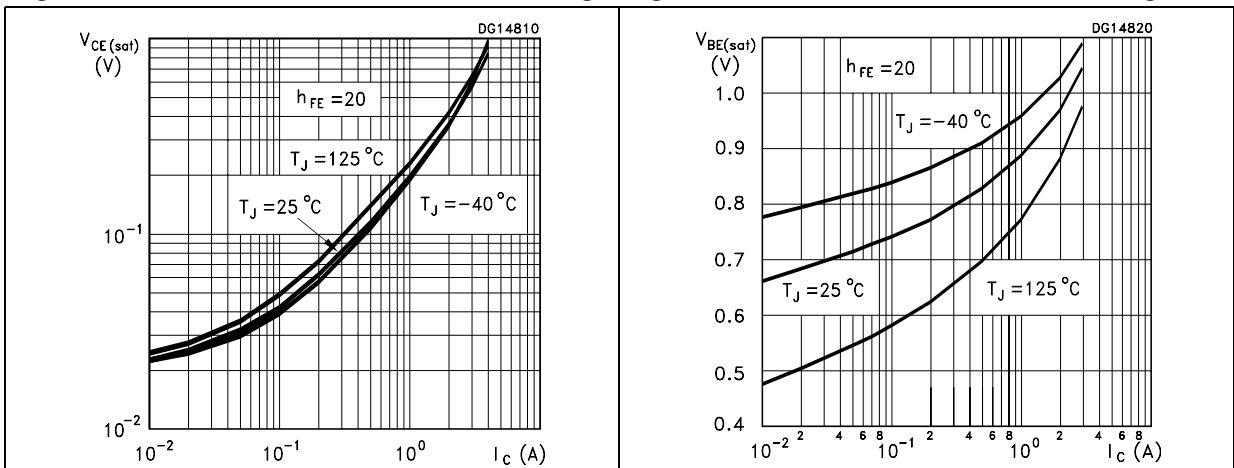


Figure 4. Collector-emitter saturation voltage Figure 5. Base-emitter saturation voltage

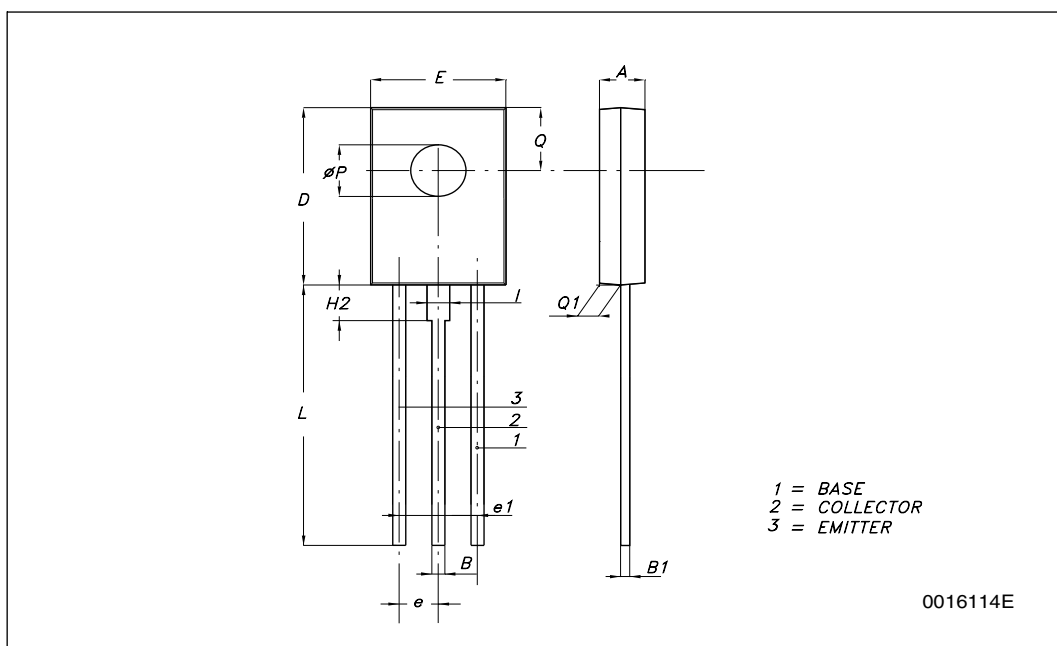


### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

**SOT-32 (TO-126) mechanical data**

DIM.	mm.		
	MIN.	TYP	MAX.
A	2.4		2.9
B	0.64		0.88
B1	0.39		0.63
D	10.5		11.05
E	7.4		7.8
e	2.04	2.29	2.54
e1	4.07	4.58	5.08
L	15.3		16
P	2.9		3.2
Q	8		
Q1	1		1.52
H2		2.15	
I	<b>z</b>		



## 4 Revision History

**Table 5. Document revision history**

Date	Revision	Changes
09-Sep-2005	2	Final version. New template
02-Oct-2007	3	Updated mechanical data

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